

$I_{F(AV)} = 8 \text{ Amp}$
 $V_R = 80 - 100V$

Major Ratings and Characteristics

Characteristics	Value	Units
$I_{F(AV)}$ Rectangular waveform	8	A
V_{RRM} range	80 - 100	V
I_{FSM} @tp = 5 μ s sine	850	A
V_F @8 Apk, $T_J = 125^\circ\text{C}$	0.58	V
T_J range	-55 to 175	$^\circ\text{C}$

Description/ Features

The 8TQ...G Schottky rectifier series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175° C junction temperature. Typical applications are in switching power supplies, converters, free-wheeling diodes, and reverse battery protection.

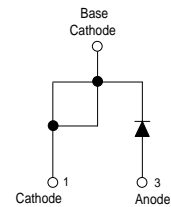
- 175° C T_J operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability

Case Styles

8TQ...G



TO-220AC



Voltage Ratings

Part number	8TQ080G	8TQ100G
V_R Max. DC Reverse Voltage (V)	80	100
V_{RWM} Max. Working Peak Reverse Voltage (V)		

Absolute Maximum Ratings

Parameters	8TQ	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current * See Fig. 5	8	A	50% duty cycle @ $T_C = 157^\circ\text{C}$, rectangular wave form
I_{FSM} Max. Peak One Cycle Non-Repetitive Surge Current * See Fig. 7	850	A	5 μs Sine or 3 μs Rect. pulse
	230		10ms Sine or 6ms Rect. pulse
E_{AS} Non-Repetitive Avalanche Energy	7.50	mJ	$T_J = 25^\circ\text{C}$, $I_{AS} = 0.50\text{Amps}$, $L = 60\text{mH}$
I_{AR} Repetitive Avalanche Current	0.50	A	Current decaying linearly to zero in 1 μsec Frequency limited by T_J max. $V_A = 1.5 \times V_R$ typical

Electrical Specifications

Parameters	8TQ	Units	Conditions
V_{FM} Max. Forward Voltage Drop (1) * See Fig. 1	0.72	V	@ 8A
	0.88	V	@ 16A
	0.58	V	@ 8A
	0.69	V	@ 16A
I_{RM} Max. Reverse Leakage Current (1) * See Fig. 2	0.28	mA	$T_J = 25^\circ\text{C}$
	7	mA	$T_J = 125^\circ\text{C}$
C_T Max. Junction Capacitance	500	pF	$V_R = 5V_{DC}$ (test signal range 100Khz to 1Mhz) 25°C
L_S Typical Series Inductance	8	nH	Measured lead to lead 5mm from package body
dv/dt Max. Voltage Rate of Change (Rated V_R)	10000	V/ μs	

(1) Pulse Width < 300 μs , Duty Cycle < 2%

Thermal-Mechanical Specifications

Parameters	8TQ	Units	Conditions
T_J Max. Junction Temperature Range	-55 to 175	$^\circ\text{C}$	
T_{stg} Max. Storage Temperature Range	-55 to 175	$^\circ\text{C}$	
R_{thJC} Max. Thermal Resistance Junction to Case	2.0	$^\circ\text{C/W}$	DC operation * See Fig. 4
R_{thCS} Typical Thermal Resistance, Case to Heatsink	0.50	$^\circ\text{C/W}$	Mounting surface, smooth and greased
wt Approximate Weight	2 (0.07)	g (oz.)	
T Mounting Torque	Min.	6 (5)	Kg-cm (lbf-in)
	Max.	12 (10)	
Device Marking	8TQ...G		

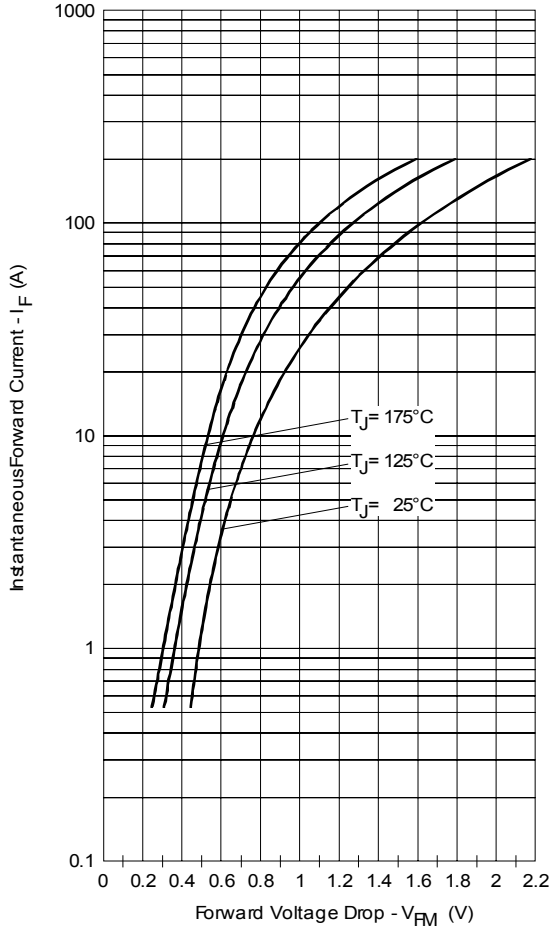


Fig. 1 - Maximum Forward Voltage Drop Characteristics

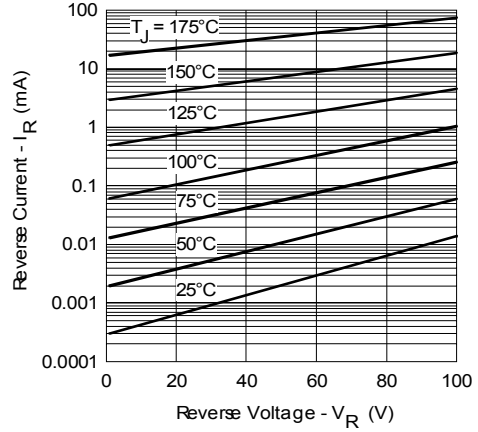


Fig. 2 - Typical Values of Reverse Current Vs. Reverse Voltage

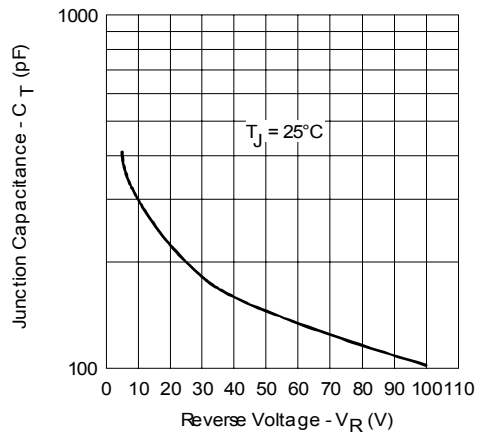


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

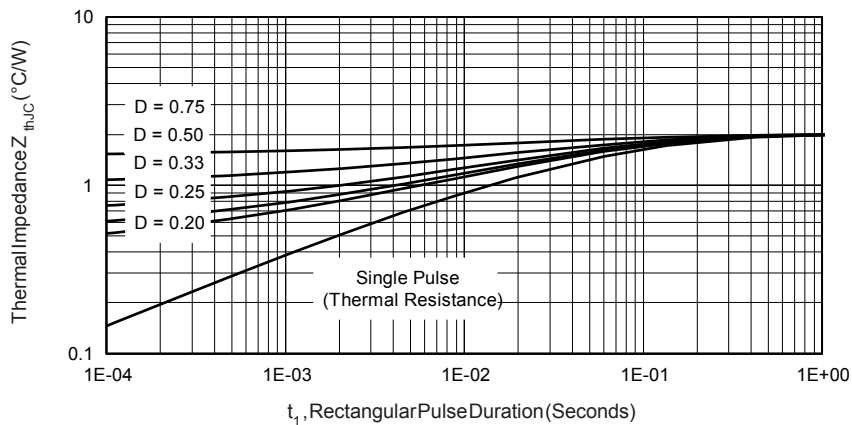


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

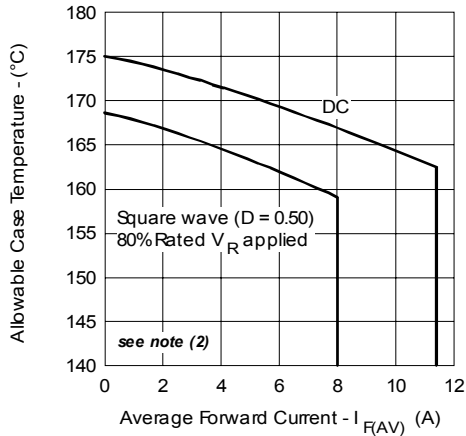


Fig. 5 - Maximum Allowable Case Temperature Vs. Average Forward Current

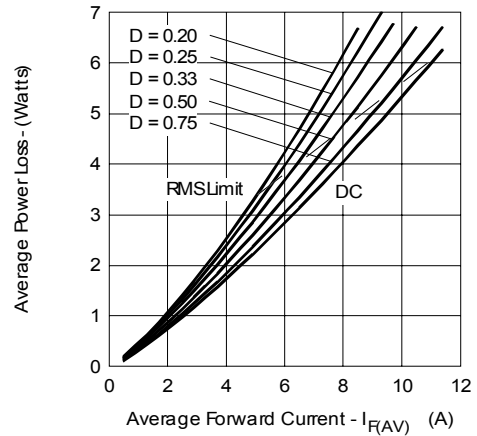


Fig. 6 - Forward Power Loss Characteristics

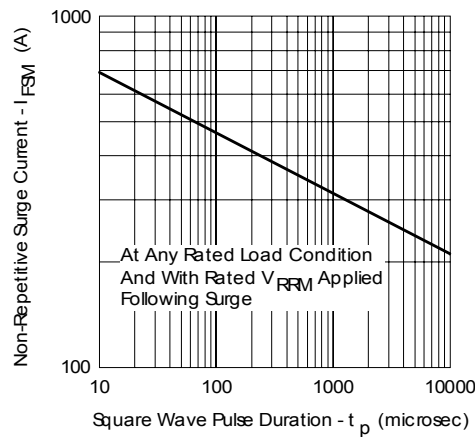


Fig. 7 - Maximum Non-Repetitive Surge Current

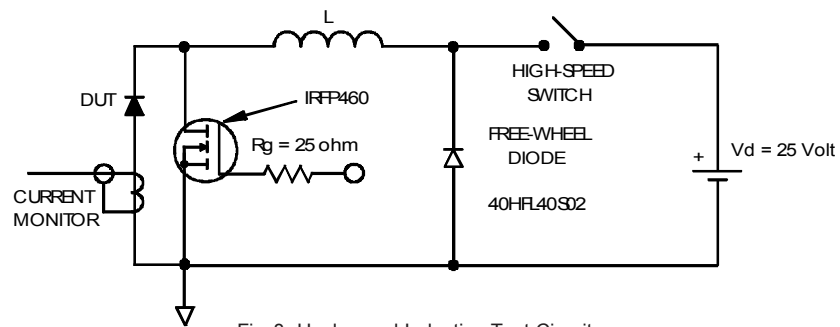


Fig. 8 - Unclamped Inductive Test Circuit

(2) Formula used: $T_c = T_j - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = Forward Power Loss = $I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$ (see Fig. 6);

Pd_{REV} = Inverse Power Loss = $V_{R1} \times I_{R1} (1 - D)$; $I_{R1} @ V_{R1} = 80\%$ rated V_R

Outline Table

NOTES:

- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 6.- CONTROLLING DIMENSION - INCHES.
- 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1 AND SINGULATION IRREGULARITIES ARE ALLOWED.
- 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
- 9.- OUTLINE CONFORMS TO JEDEC TO-220, 32 (mm) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	5
b1	0.38	0.97	.015	.038	
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	-	6.35	-	.250	3
L3	1.78	2.13	.070	.084	
L4	0.76	1.27	.030	.050	3
Q	3.53	3.73	.139	.147	
Q	2.54	3.05	.100	.120	

LEAD ASSIGNMENTS
DOCS
1-2 - CATHODE
3 - ANODE

Conform to JEDEC outline TO-220AB
Dimensions in millimeters and (inches)

Part Marking Information

EXAMPLE: THIS IS A 8TQ100G
LOT CODE 1789
ASSEMBLED ON WW 19, 2001
IN THE ASSEMBLY LINE "C"

INTERNATIONAL RECTIFIER LOGO

PART NUMBER
G = Schottky Generation

DATE CODE
YEAR 1 = 2001
WEEK 19
LINE C

ASSEMBLY LOT CODE

Ordering Information Table

Device Code					
8	T	Q	100	G	-
①	②	③	④	⑤	⑥

<p>1 - Current Rating (8 = 8A)</p> <p>2 - T = TO-220</p> <p>3 - Q = Schottky Q Series</p> <p>4 - Voltage Ratings</p> <p>5 - G = Schottky Generation</p> <p>6 -</p> <ul style="list-style-type: none"> • none = Standard Production • PbF = Lead-Free 	<div style="border: 1px solid black; padding: 5px; display: inline-block;"> 080 = 80V 100 = 100V </div>
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Tube Standard Pack Quantity : 50 pieces

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8TQ100
*****
* This model has been developed by *
* Wizard SPICE MODEL GENERATOR (1999) *
* (International Rectifier Corporation) *
* Contain Proprietary Information *
*****
* SPICE Model Diode is composed by a *
* simple diode plus paralalled VCG2T *
*****
.SUBCKT 8TQ100 ANO CAT
D1 ANO 1 DMOD (0.07089)
*Define diode model
.MODEL DMOD D(IS=1.15938021883115E-03A,N=1.95244918720315,BV=120V,
+ IBV=5.37891460505463A,RS= 0.00127602,CJO=9.9895753025115E-09,
+ VJ=2.30070034831946,XTI=2, EG=0.758916909331649)
*****
*Implementation of VCG2T
VX 1 2 DC 0V
R1 2 CAT TRES 1E-6
.MODEL TRES RES(R=1,TC1=-90.2420977904848)
GP1 ANO CAT VALUE={-ABS(I(VX))*(EXP(((1.635248E-02/-90.2421)*(V(2,CAT)*1E6)/(I(VX)+1E-6)-1))+1)*4.011038E-03*ABS(V(ANO,CAT))-1}}
*****
.ENDS 8TQ100

Thermal Model Subcircuit
.SUBCKT 8TQ100 5 1

CTHERM1 5 4 1.45E+00
CTHERM2 4 3 4.54E+00
CTHERM3 3 2 1.09E+01
CTHERM4 2 1 1.01E+02

RTHERM1 5 4 2.49E+00
RTHERM2 4 3 5.20E-04
RTHERM1 3 2 5.43E-01
RTHERM1 2 1 3.05E-02

.ENDS 8TQ100
    
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Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

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